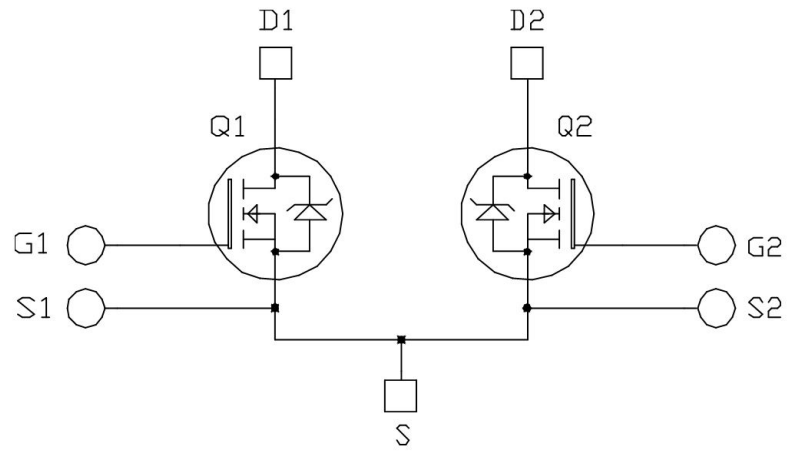
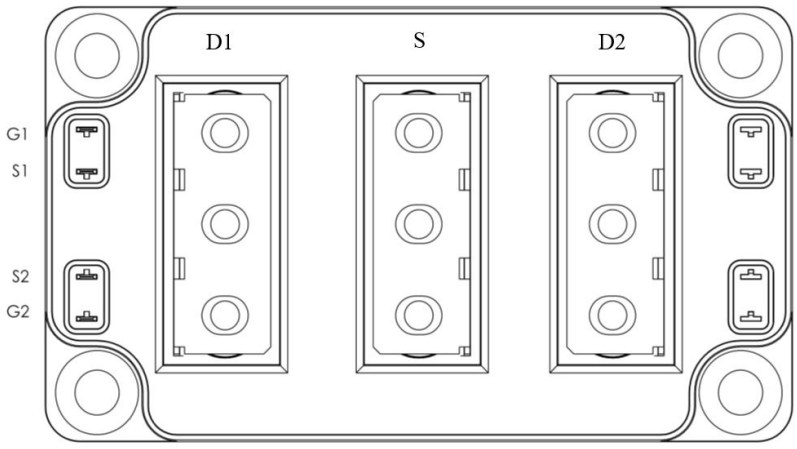
MSCSM170DUM039AG

Dual Common Source SiC MOSFET Power Module

Product Overview

The MSCSM170DUM039AG device is a 1700V/523A dual common source silicon carbide (SiC) MOSFET power module.





Note: All ratings at T_J = 25 °C, unless otherwise specified.

⚠ CAUTION These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

Features

The following are the key features of MSCSM170DUM039AG device:

- SiC Power MOSFET
  - Low $R_{DS(on)}$
  - High temperature performance
- Kelvin source for easy drive
- Low stray inductance
- High level of integration
- Aluminum Nitride (AlN) substrate for improved thermal performance
- M5 power connectors

Benefits

The following are the benefits of MSCSM170DUM039AG device:

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Low profile
- RoHS compliant

Application

The following are the applications of MSCSM170DUM039AG device:

- AC switches
- Switched mode power supplies
- Uninterruptible power supplies

1. Electrical Specifications

This section provides the electrical specifications of the MSCSM170DUM039AG device.

1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings of MSCSM170DUM039AG device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter		Maximum Ratings	Unit
V_{DSS}	Drain-Source voltage		1700	V
I_D	Continuous drain current	T_C = 25 °C	523	A
		T_C = 80 °C	416	
I_{DM}	Pulsed drain current		1000	
V_{GSmax}	Gate-Source voltage		–10/23	V
$R_{DS(on)}$	Drain-Source ON resistance		5	mΩ
P_D	Power dissipation	T_C = 25 °C	2400	W

The following table lists the electrical characteristics of MSCSM170DUM039AG device.

Table 1-2. Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0V V_{DS} = 1700V		—	90	900	µA
$R_{DS(on)}$	Drain–Source on resistance	V_{GS} = 20V I_D = 270A	T_J = 25 °C	—	3.9	5	mΩ
			T_J = 175 °C	—	6.8	—	
$V_{GS(th)}$	Gate threshold voltage	V_{GS} = V_{DS} I_D = 22.5 mA		1.8	3.3	—	V
I_{GSS}	Gate–Source leakage current	V_{GS} = 20V V_{DS} = 0V		—	—	900	nA

The following table lists the dynamic characteristics of MSCSM170DUM039AG device.

Table 1-3. Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{GS} = 0V		—	29.7	—	nF
C_{oss}	Output capacitance	V_{DS} = 1000V		—	1.3	—	
C_{rss}	Reverse transfer capacitance	f = 1 MHz		—	0.09	—	
Q_g	Total gate charge	V_{GS} = –5V/20V		—	1602	—	nC
Q_{gs}	Gate-Source charge	V_{Bus} = 850V		—	441	—	
Q_{gd}	Gate-Drain charge	I_D = 270A		—	243	—	
$T_{d(on)}$	Turn-on delay time	V_{GS} = –5V/20V	T_J = 150 °C	—	75	—	ns
T_r	Rise time	V_{Bus} = 900V		—	75	—	
$T_{d(off)}$	Turn-off delay time	I_D = 450A		—	153	—	
T_f	Fall time	R_{Gon} = 3.2Ω			56	—	
		R_{Goff} = 1.8Ω					
E_{on}	Turn-on energy	V_{GS} = –5V/20V	T_J = 150 °C	—	24.3	—	mJ
E_{off}	Turn-off energy	V_{Bus} = 900V	T_J = 150 °C	—	10.8	—	
		I_D = 450A					
		R_{Gon} = 3.2Ω					
		R_{Goff} = 1.8Ω					
R_{Gint}	Internal gate resistance			—	0.65	—	Ω
R_{thJC}	Junction-to-case thermal resistance			—	—	0.063	°C/W

The following table lists the body diode ratings and characteristics of MSCSM170DUM039AG device.

Table 1-4. Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
V_{SD}	Diode forward voltage	V_{GS} = 0V I_{SD} = 270A	—	3.7	—	V
		V_{GS} = –5V I_{SD} = 270A	—	3.9	—	
t_{rr}	Reverse recovery time	I_{SD} = 270A	—	27	—	ns
Q_{rr}	Reverse recovery charge	V_{GS} = –5V	—	5.9	—	µC
I_{rr}	Reverse recovery current	V_R = 900V di_F/dt = 9000A/µs	—	414	—	A

1.2 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM170DUM039AG device.

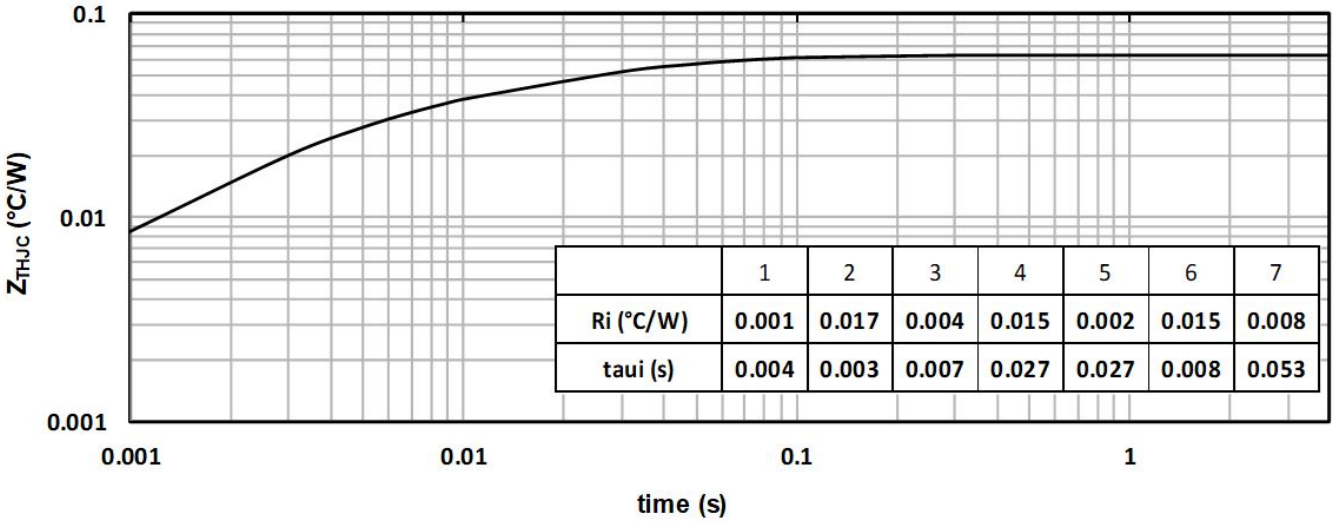
Table 1-5. Thermal and Package Characteristics

Symbol	Characteristic			Min.	Max.	Unit
V_{ISOL}	RMS isolation voltage, any terminal to case t = 1 min, 50 Hz/60 Hz			4000	—	V
T_J	Operating junction temperature range			–40	175	°C
T_{JOP}	Recommended junction temperature under switching conditions			–40	T_{Jmax}–25	
T_{STG}	Storage case temperature			–40	125	
T_C	Operating case temperature			–40	125	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package weight			—	320	g

1.3 Typical SiC MOSFET Performance Curve (Per SiC MOSFET)

This section shows the typical SiC MOSFET performance curves of the MSCSM170DUM039AG device.

Figure 1-1. Junction-to-Heatsink Thermal Impedance



	1	2	3	4	5	6	7
Ri (°C/W)	0.001	0.017	0.004	0.015	0.002	0.015	0.008
taui (s)	0.004	0.003	0.007	0.027	0.027	0.008	0.053

Figure 1-2. Output Characteristics, T_J = 25 °C

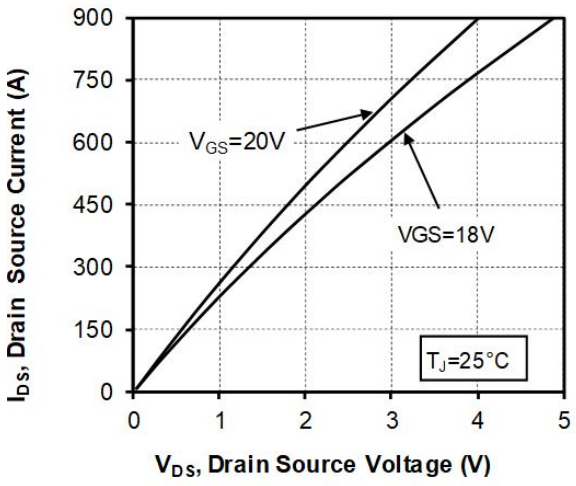


Figure 1-3. Output Characteristics, T_J = 175 °C

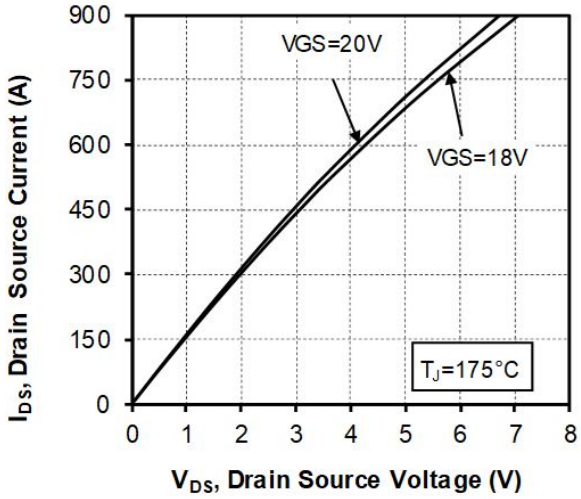


Figure 1-4. Normalized $R_{DS(on)}$ vs. Temperature

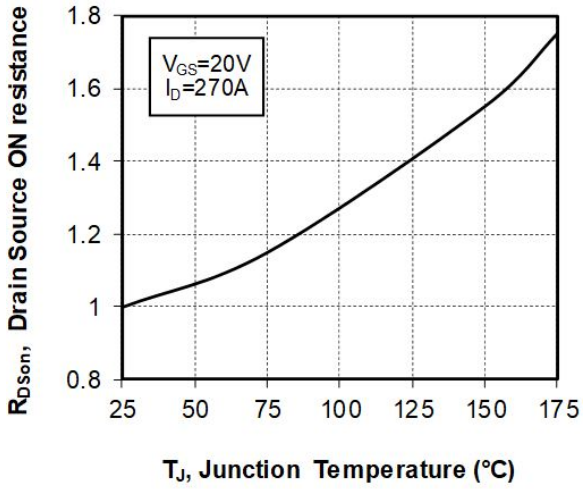


Figure 1-5. Transfer Characteristics

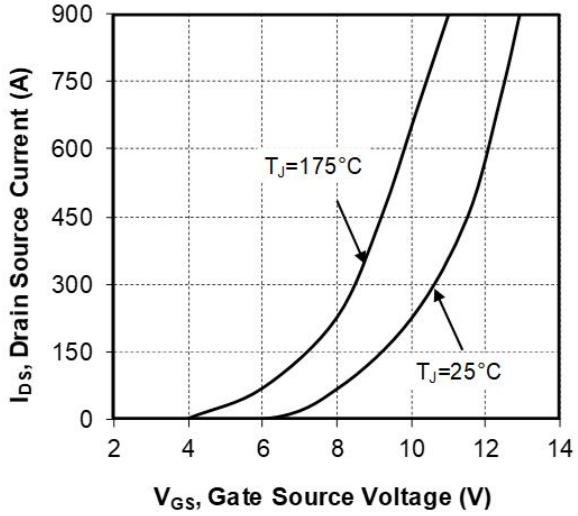


Figure 1-6. Switching Energy vs. Rg

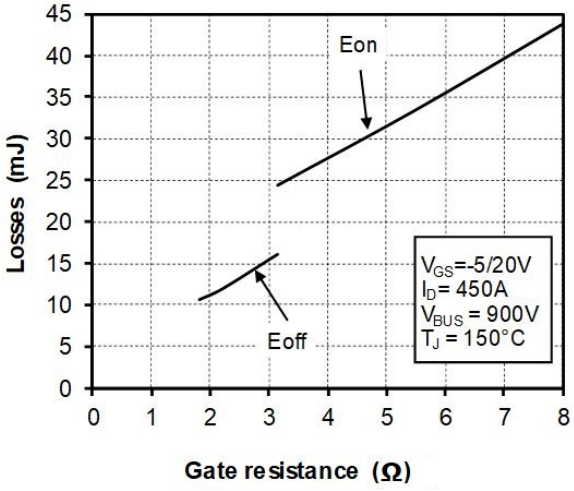


Figure 1-7. Switching Energy vs. Current

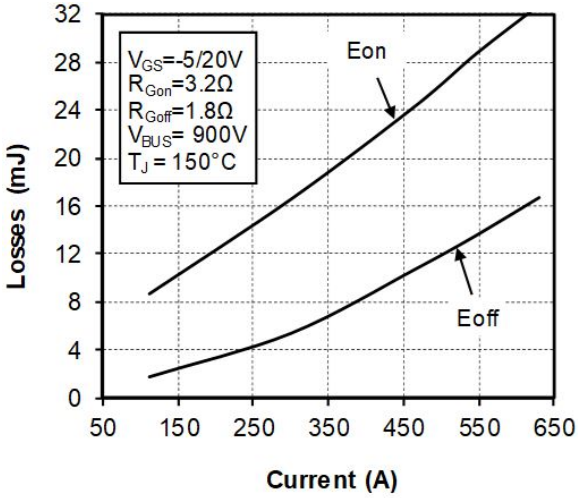


Figure 1-8. Capacitance vs. Drain Source Voltage

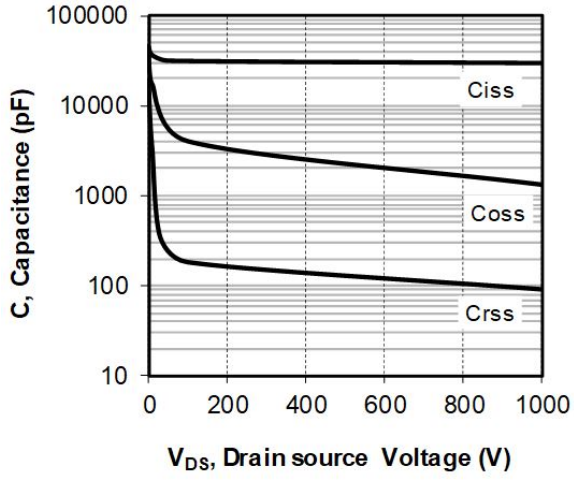


Figure 1-9. Gate Charge vs. Gate Source Voltage

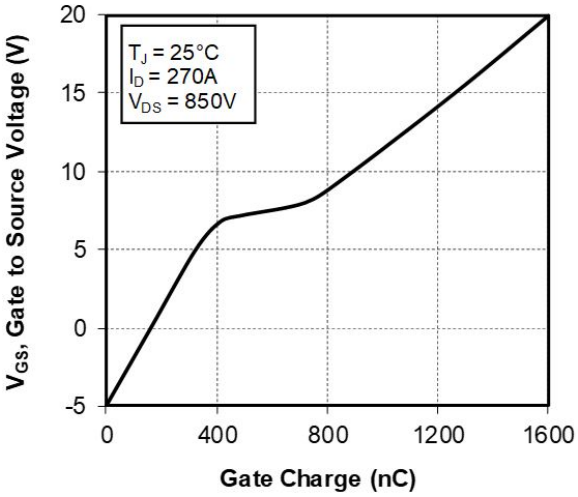


Figure 1-10. Body Diode Characteristics, T_J = 25 °C

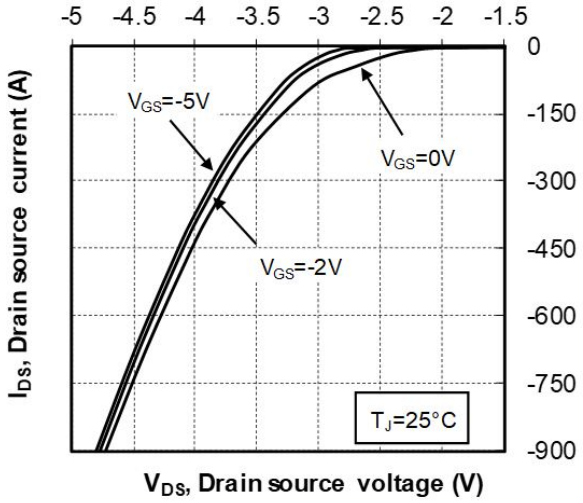


Figure 1-11. 3rd Quadrant Characteristics, T_J = 25 °C

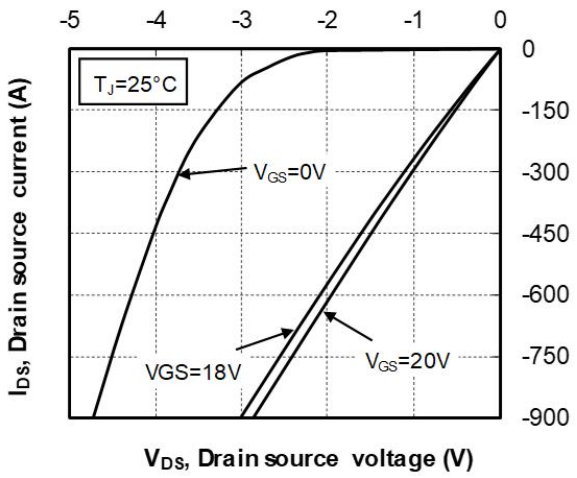


Figure 1-12. Body Diode Characteristics, T_J = 175 °C

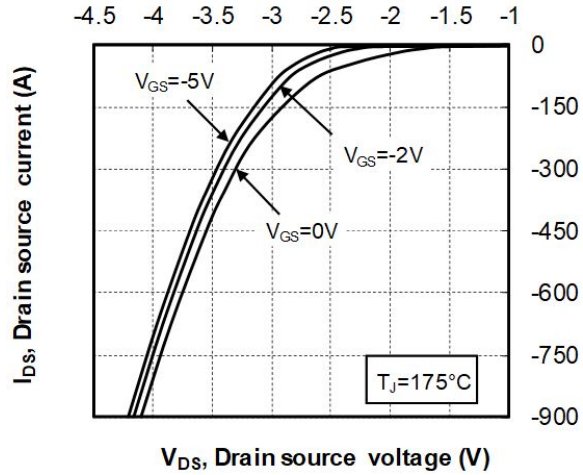


Figure 1-13. 3rd Quadrant Characteristics, T_J = 175 °C

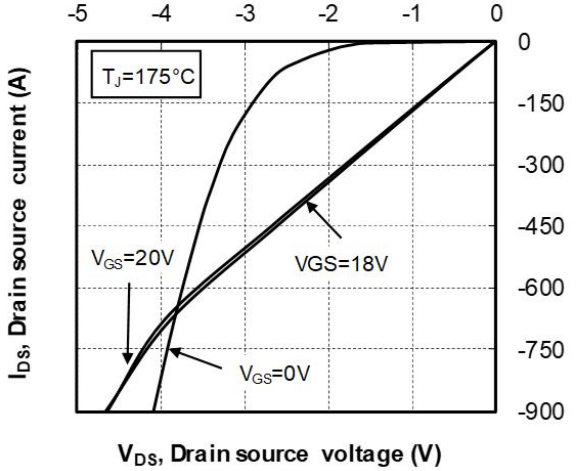
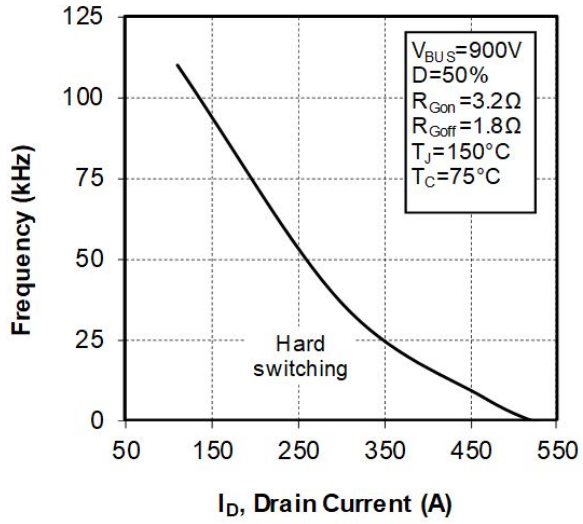


Figure 1-14. Operating Frequency vs. Drain Current



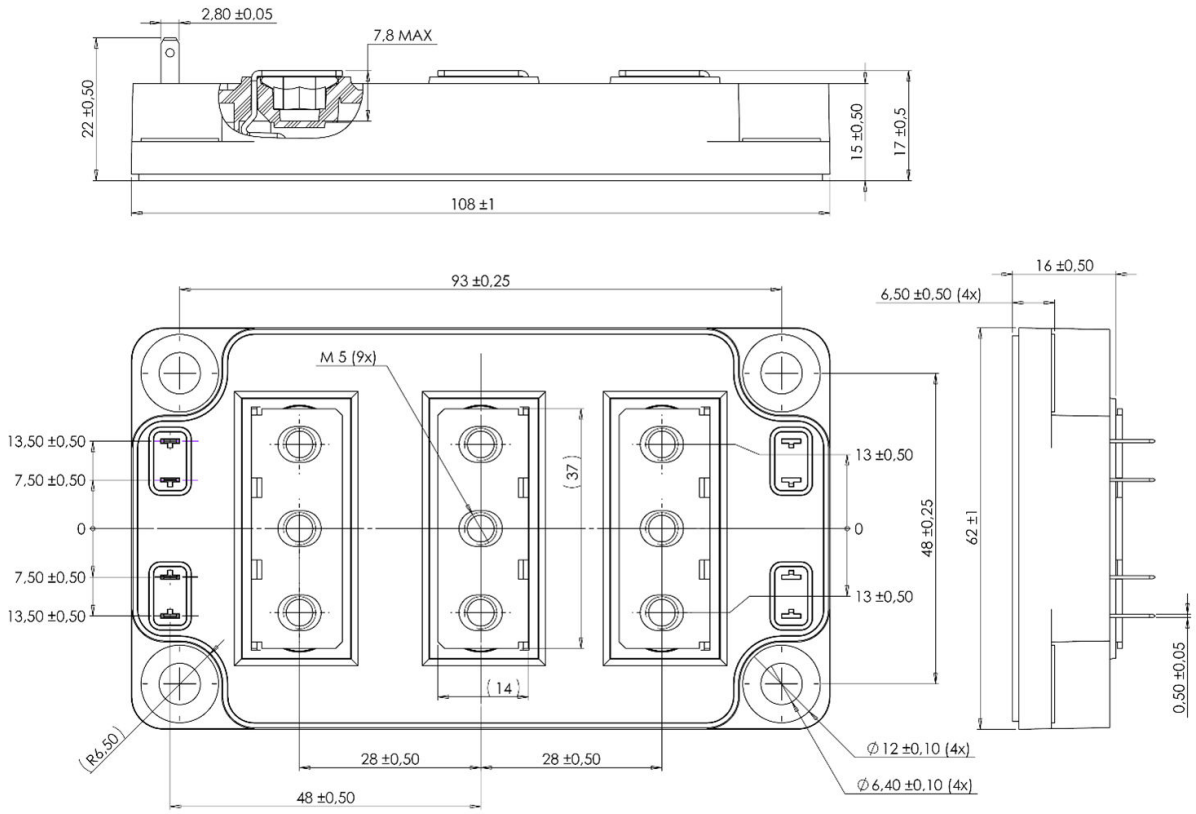
2. Package Specifications

The following section shows the package specification of the MSCSM170DUM039AG device.

2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM170DUM039AG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



3. Revision History

Revision	Date	Description
A	12/2021	Initial Revision

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